

ZXTP25060BFH

60V, SOT23, PNP medium power transistor

Summary

$BV_{(BR)CEX} > -100V$, $BV_{(BR)CEO} > -60V$

$BV_{(BR)ECO} > -7V$;

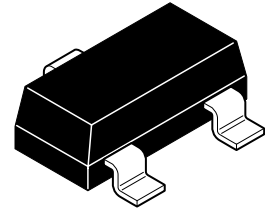
$I_{C(cont)} = -3A$;

$R_{CE(sat)} = 58\ m\Omega$ typical;

$V_{CE(sat)} < -85mV$ @ -1A ;

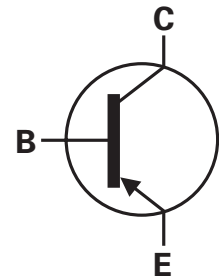
$P_D = 1.25W$

Complementary part number ZXTN25060BFH



Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

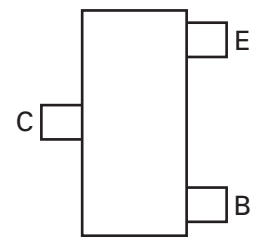


Features

- Higher power dissipation SOT23 package
- High peak current
- Low saturation voltage
- 100V forward blocking voltage
- 7V reverse blocking voltage

Applications

- MOSFET gate drivers
- Power switches
- Motor control



Pinout - top view

Ordering information

| Device | Reel size (inches) | Tape width | Quantity per reel |
|----------------|--------------------|------------|-------------------|
| ZXTP25060BFHTA | 7 | 8mm | 3,000 |

Device marking

028

ZXTP25060BFH

Absolute maximum ratings

| Parameter | Symbol | Limit | Unit |
|--|----------------|--------------|------------|
| Collector-base voltage | V_{CBO} | -100 | V |
| Collector-emitter voltage (forward blocking) | V_{CEX} | -100 | V |
| Collector-emitter voltage | V_{CEO} | -60 | V |
| Emitter-collector voltage (reverse blocking) | V_{ECO} | -7 | V |
| Emitter-base voltage | V_{EBO} | -7 | V |
| Continuous collector current ^(a) | I_C | -3 | A |
| Peak pulse current | I_{CM} | -9 | A |
| Power dissipation at $T_A = 25^\circ\text{C}$ ^(a) Linear derating factor | P_D | 0.73 5.84 | W mW/°C |
| Power dissipation at $T_A = 25^\circ\text{C}$ ^(b) Linear derating factor | P_D | 1.05 8.4 | W mW/°C |
| Power dissipation at $T_A = 25^\circ\text{C}$ ^(c) Linear derating factor | P_D | 1.25 9.6 | W mW/°C |
| Power dissipation at $T_A = 25^\circ\text{C}$ ^(d) Linear derating factor | P_D | 1.81 14.5 | W mW/°C |
| Operating and storage temperature range | T_j, T_{stg} | -55 to 150 | °C |

Thermal resistance

| Parameter | Symbol | Limit | Unit |
|------------------------------------|-----------------|-------|------|
| Junction to ambient ^(a) | $R_{\theta JA}$ | 171 | °C/W |
| Junction to ambient ^(b) | $R_{\theta JA}$ | 119 | °C/W |
| Junction to ambient ^(c) | $R_{\theta JA}$ | 100 | °C/W |
| Junction to ambient ^(d) | $R_{\theta JA}$ | 69 | °C/W |

NOTES:

(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

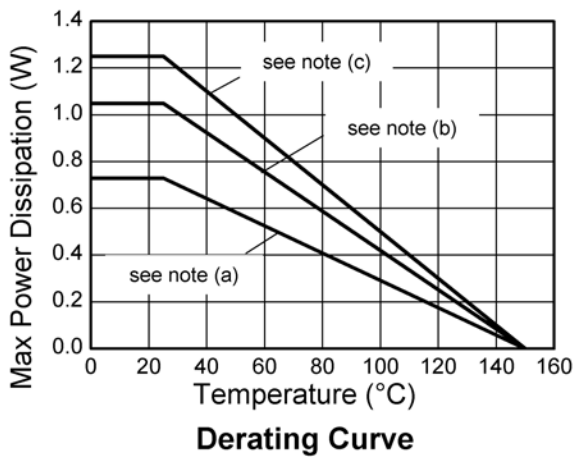
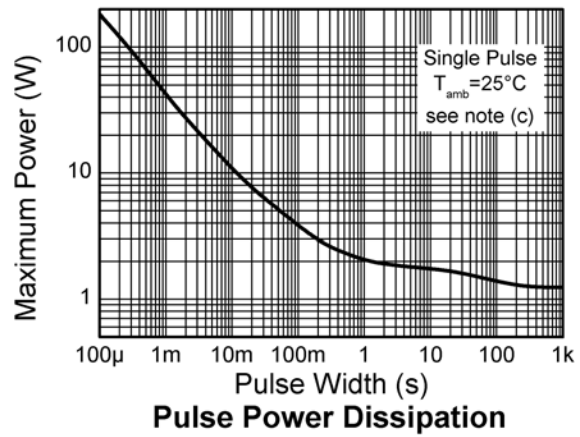
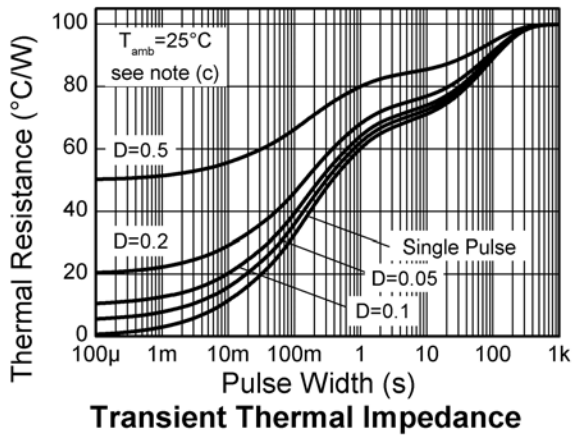
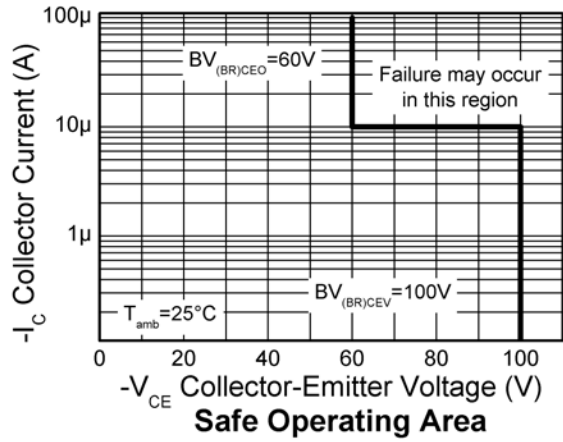
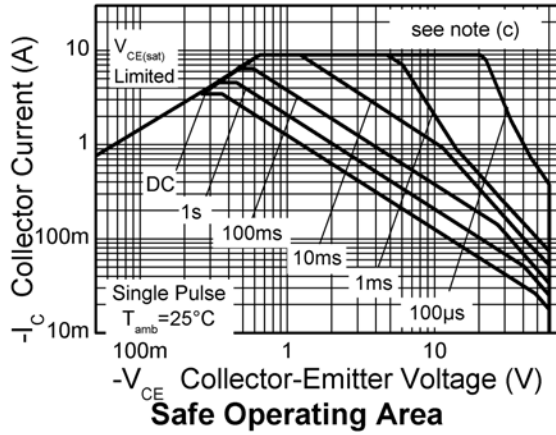
(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(d) As (c) above measured at $t < 5\text{secs}$

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Characteristics



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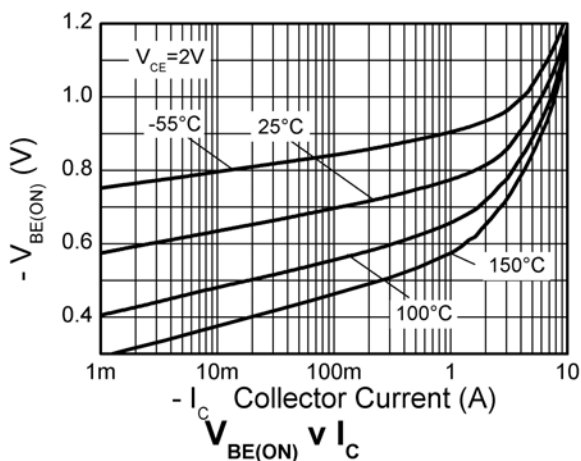
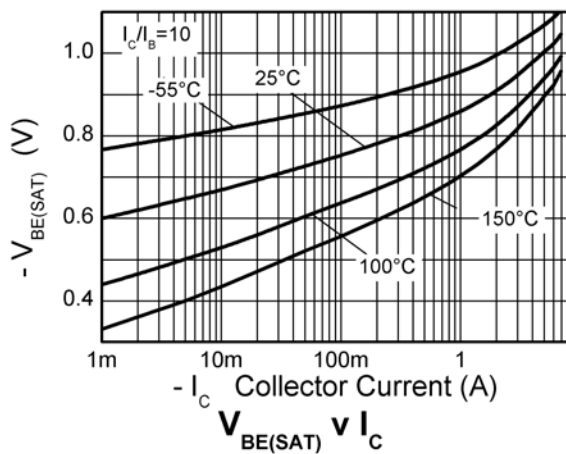
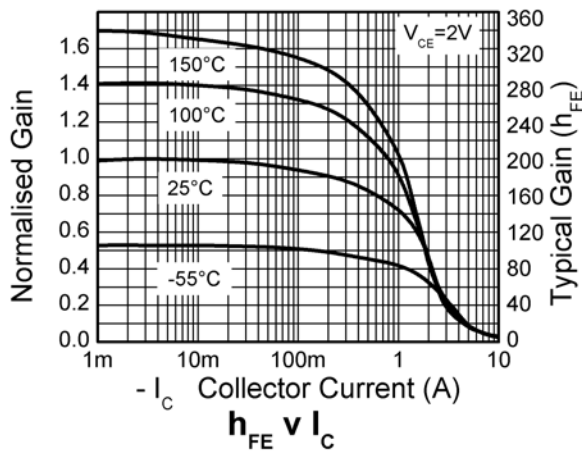
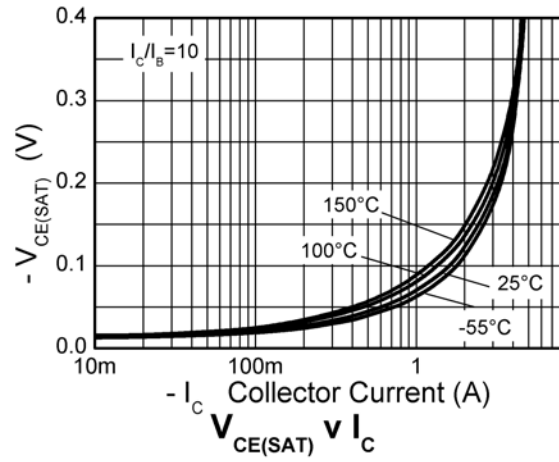
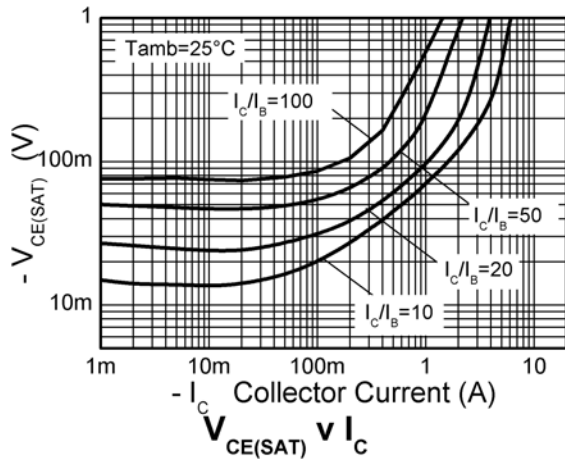
Electrical characteristics (at $T_{AMB} = 25^{\circ}\text{C}$ unless otherwise stated)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|--|---------------|------|------|------------|---------------------|---|
| Collector-base breakdown voltage | BV_{CBO} | -100 | -120 | | V | $I_C = -100\text{mA}$ |
| Collector-emitter breakdown voltage (forward blocking) | BV_{CEX} , | -100 | -120 | | V | $I_C = -100\text{mA}$, $R_{BE} < 1\text{k}\Omega$ or $-0.25\text{V} < V_{BE} < 1\text{V}$ |
| Collector-emitter breakdown voltage (base open) | BV_{CEO} | -60 | -80 | | V | $I_C = -10\text{mA}$ (*) |
| Emitter-collector breakdown voltage (reverse blocking) | BV_{ECO} | -7 | -8.6 | | V | $I_E = -100\mu\text{A}$ (*) |
| Emitter-base breakdown voltage | BV_{EBO} | -7 | -8.1 | | V | $I_E = -100\text{mA}$ |
| Collector cut-off current | I_{CBO} | | <-1 | -50 -20 | nA μA | $V_{CB} = -80\text{V}$ $V_{CB} = -80\text{V}$, $T_{AMB} = 100^{\circ}\text{C}$ |
| Collector emitter cut-off current | I_{CEX} | | - | -100 | nA | $V_{CE} = -80\text{V}$; $R_{BE} < 1\text{k}\Omega$ or $-0.25\text{V} < V_{BE} < 1\text{V}$ |
| Emitter cut-off current | I_{EBO} | | <-1 | -50 | nA | $V_{EB} = -5.6\text{V}$ |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | | -45 | -55 | mV | $I_C = -0.5\text{A}$, $I_B = -50\text{mA}$ (*) |
| | | | -100 | -135 | mV | $I_C = -0.5\text{A}$, $I_B = -10\text{mA}$ (*) |
| | | | -70 | -85 | mV | $I_C = -1\text{A}$, $I_B = -100\text{mA}$ (*) |
| | | | -175 | -235 | mV | $I_C = -3\text{A}$, $I_B = -300\text{mA}$ (*) |
| Base-emitter saturation voltage | $V_{BE(sat)}$ | | -940 | -1040 | mV | $I_C = -3\text{A}$, $I_B = -300\text{mA}$ (*) |
| Base-emitter turn-on voltage | $V_{BE(on)}$ | | -830 | -930 | mV | $I_C = -3\text{A}$, $V_{CE} = -2\text{V}$ (*) |
| Static forward current transfer ratio | h_{FE} | 100 | 200 | 300 | | $I_C = -10\text{mA}$, $V_{CE} = -2\text{V}$ (*) |
| | | 75 | 150 | | | $I_C = -1\text{A}$, $V_{CE} = -2\text{V}$ (*) |
| | | 30 | 60 | | | $I_C = -3\text{A}$, $V_{CE} = -2\text{V}$ (*) |
| Transition frequency | f_T | | 250 | | MHz | $I_C = -100\text{mA}$, $V_{CE} = -5\text{V}$ $f = 100\text{MHz}$ |
| Output capacitance | C_{OBO} | | 17.6 | 30 | pF | $V_{CB} = -10\text{V}$, $f = 1\text{MHz}$ (*) |
| Turn-on time | $t_{(on)}$ | | 26.5 | | ns | $V_{CC} = -10\text{V}$. $I_C = -500\text{mA}$, |
| Turn-off time | $t_{(off)}$ | | 291 | | ns | $I_{B1} = I_{B2} = -50\text{mA}$. |

NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

Typical characteristics



ZXTP25060BFH

Package outline - SOT23



| Dim. | Millimeters | | Inches | | Dim. | Millimeters | | Inches | |
|------|-------------|------|-----------|--------|------|-------------|------|------------|--------|
| | Min. | Max. | Min. | Max. | | Min. | Max. | Max. | Max. |
| A | 2.67 | 3.05 | 0.105 | 0.120 | H | 0.33 | 0.51 | 0.013 | 0.020 |
| B | 1.20 | 1.40 | 0.047 | 0.055 | K | 0.01 | 0.10 | 0.0004 | 0.004 |
| C | - | 1.10 | - | 0.043 | L | 2.10 | 2.50 | 0.083 | 0.0985 |
| D | 0.37 | 0.53 | 0.015 | 0.021 | M | 0.45 | 0.64 | 0.018 | 0.025 |
| F | 0.085 | 0.15 | 0.0034 | 0.0059 | N | 0.95 NOM | | 0.0375 NOM | |
| G | 1.90 NOM | | 0.075 NOM | | - | - | - | - | - |

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

| Europe | Americas | Asia Pacific | Corporate Headquarters |
|---|---|--|--|
| Zetex GmbH Streitfeldstraße 19 D-81673 München Germany | Zetex Inc 700 Veterans Memorial Highway Hauppauge, NY 11788 USA | Zetex (Asia Ltd) 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong | Zetex Semiconductors plc Zetex Technology Park, Chadderton Oldham, OL9 9LL United Kingdom |
| Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 europe.sales@zetex.com | Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 usa.sales@zetex.com | Telephone: (852) 26100 611 Fax: (852) 24250 494 asia.sales@zetex.com | Telephone: (44) 161 622 4444 Fax: (44) 161 622 4446 hq@zetex.com |

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